Octal 3-State Noninverting Bus Transceiver

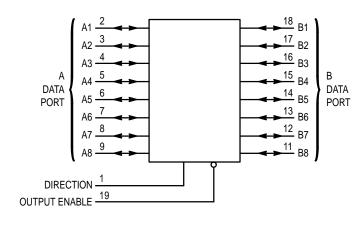
High-Performance Silicon-Gate CMOS

The MC54/74HC245A is identical in pinout to the LS245. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC245A is a 3-state noninverting transceiver that is used for 2-way asynchronous communication between data buses. The device has an active-low Output Enable pin, which is used to place the I/O ports into high-impedance states. The Direction control determines whether data flows from A to B or from B to A.

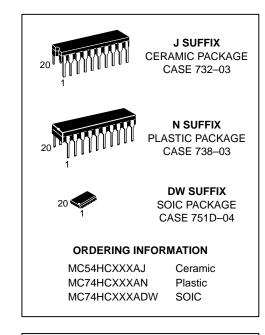
- · Output Drive Capability: 15 LSTTL Loads
- · Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μA
- · High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 308 FETs or 77 Equivalent Gates

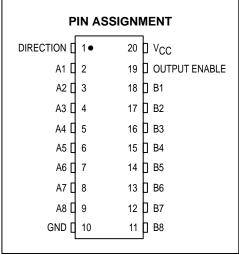
LOGIC DIAGRAM



PIN 10 = GND PIN 20 = V_{CC}

MC54/74HC245A





FUNCTION TABLE

| Contro | l Inputs | |
|------------------|-----------|---------------------------------------|
| Output Enable | Direction | Operation |
| L | L | Data Transmitted from Bus B to Bus A |
| L | Н | Data Transmitted from Bus A to Bus B |
| Н | Х | Buses Isolated (High-Impedance State) |

X = don't care



MAXIMUM RATINGS*

| Symbol | Parameter | Value | Unit |
|------------------|---|--------------------------------|------|
| VCC | DC Supply Voltage (Referenced to GND) | - 0.5 to + 7.0 | V |
| V _{in} | DC Input Voltage (Referenced to GND) | - 1.5 to V _{CC} + 1.5 | V |
| V _{I/O} | DC Output Voltage (Referenced to GND) | -0.5 to V _{CC} + 0.5 | V |
| l _{in} | DC Input Current, per Pin | ± 20 | mA |
| I _{I/O} | DC Output Current, per Pin | ± 35 | mA |
| Icc | DC Supply Current, V _{CC} and GND Pins | ± 75 | mA |
| PD | Power Dissipation in Still Air, Plastic or Ceramic DIP† SOIC Package† | 750 500 | mW |
| T _{stg} | Storage Temperature | - 65 to + 150 | °C |
| TL | Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package) (Ceramic DIP) | 260 300 | °C |

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq VCC. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or VCC).

Unused outputs must be left open.

Ceramic DIP: - 10 mW/°C from 100° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | | | Max | Unit |
|------------------------------------|--|--|-------------|--------------------|------|
| VCC | DC Supply Voltage (Referenced to GND) | | | 6.0 | V |
| V _{in} , V _{out} | DC Input Voltage, Output Voltage (Referenced to GND) | | | Vcc | V |
| TA | Operating Temperature, All Package Types | | | + 125 | °C |
| t _r , t _f | Input Rise and Fall Time V((Figure 1) V(V(| CC = 2.0 V CC = 4.5 V CC = 6.0 V | 0 0 0 | 1000 500 400 | ns |

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

| | | | | Gu | Guaranteed Limit | | |
|-----------------|--|--|-------------------|--------------------|--------------------|--------------------|------|
| Symbol | Parameter | Test Conditions | v _{CC} | – 55 to 25°C | ≤ 85°C | ≤ 125°C | Unit |
| VIH | Minimum High-Level Input Voltage | $V_{Out} = 0.1 \text{ V or V}_{CC} - 0.1 \text{ V}$ $ I_{Out} \le 20 \mu\text{A}$ | 2.0 4.5 6.0 | 1.5 3.15 4.2 | 1.5 3.15 4.2 | 1.5 3.15 4.2 | V |
| V _{IL} | Maximum Low–Level Input Voltage | $V_{Out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{Out} \le 20 \mu\text{A}$ | 2.0 4.5 6.0 | 0.5 1.35 1.8 | 0.5 1.35 1.8 | 0.5 1.35 1.8 | V |
| VOH | Minimum High-Level Output Voltage | $V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}}$ $ I_{\text{out}} \le 20 \mu\text{A}$ | 2.0 4.5 6.0 | 1.9 4.4 5.9 | 1.9 4.4 5.9 | 1.9 4.4 5.9 | V |
| | | $V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} I_{\text{Out}} \le 6.0 \text{ mA} \\ I_{\text{Out}} \le 7.8 \text{ mA}$ | 4.5 6.0 | 3.98 5.48 | 3.84 5.34 | 3.70 5.20 | |
| V _{OL} | Maximum Low–Level Output Voltage | $V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}}$ $ I_{\text{out}} \le 20 \mu\text{A}$ | 2.0 4.5 6.0 | 0.1 0.1 0.1 | 0.1 0.1 0.1 | 0.1 0.1 0.1 | V |
| | | $V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} I_{\text{Out}} \le 6.0 \text{ mA} \\ I_{\text{Out}} \le 7.8 \text{ mA}$ | 4.5 6.0 | 0.26 0.26 | 0.33 0.33 | 0.40 0.40 | |
| l _{in} | Maximum Input Leakage Current | V _{in} = V _{CC} or GND, Pin 1 or 19 | 6.0 | ± 0.1 | ± 1.0 | ± 1.0 | μΑ |
| loz | Maximum Three–State Leakage Current | Output in High-Impedance State $V_{\text{in}} = V_{\text{IL}} \text{ or } V_{\text{IH}}$ $V_{\text{out}} = V_{\text{CC}} \text{ or GND, I/O Pins}$ | 6.0 | ± 0.5 | ± 5.0 | ± 10 | μΑ |
| Icc | Maximum Quiescent Supply Current (per Package) | $V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$ | 6.0 | 4 | 40 | 160 | μА |

NOTE: Information on typical parametric values and high frequency or heavy load considerations can be found in Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).

MOTOROLA 2

^{*} Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

[†]Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6 \text{ ns}$)

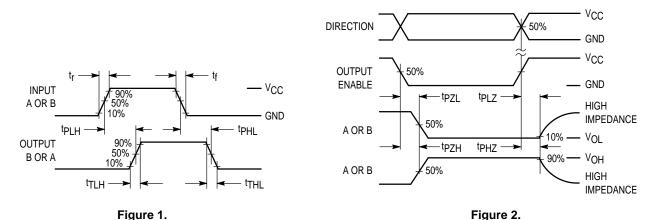
| | | | Guaranteed Limit | | | |
|--|---|-------------------|------------------|-----------------|-----------------|------|
| Symbol | Parameter | V _{CC} | – 55 to 25°C | ≤ 85°C | ≤ 125°C | Unit |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, A to B, B to A (Figures 1 and 3) | 2.0 4.5 6.0 | 75 15 13 | 95 19 16 | 110 22 19 | ns |
| t _{PLZ} , t _{PHZ} | Maximum Propagation Delay, Direction or Output Enable to A or B (Figures 2 and 4) | 2.0 4.5 6.0 | 110 22 19 | 140 28 24 | 165 33 28 | ns |
| tPZL, tPZH | Maximum Propagation Delay, Output Enable to A or B (Figures 2 and 4) | 2.0 4.5 6.0 | 110 22 19 | 140 28 24 | 165 33 28 | ns |
| tTLH, tTHL | Maximum Output Transition Time, Any Output (Figures 1 and 3) | 2.0 4.5 6.0 | 60 12 10 | 75 15 13 | 90 18 15 | ns |
| C _{in} | Maximum Input Capacitance (Pin 1 or Pin 19) | | 10 | 10 | 10 | pF |
| C _{out} | Maximum Three–State I/O Capacitance (I/O in High–Impedance State) | _ | 15 | 15 | 15 | pF |

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).

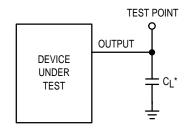
| | | Typical @ 25°C, $V_{CC} = 5.0 \text{ V}$ | | 1 |
|-----------------|--|--|----|---|
| C _{PD} | Power Dissipation Capacitance (Per Transceiver Channel)* | 40 | pF | l |

^{*} Used to determine the no–load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).

SWITCHING WAVEFORMS



TEST CIRCUITS



^{*} Includes all probe and jig capacitance

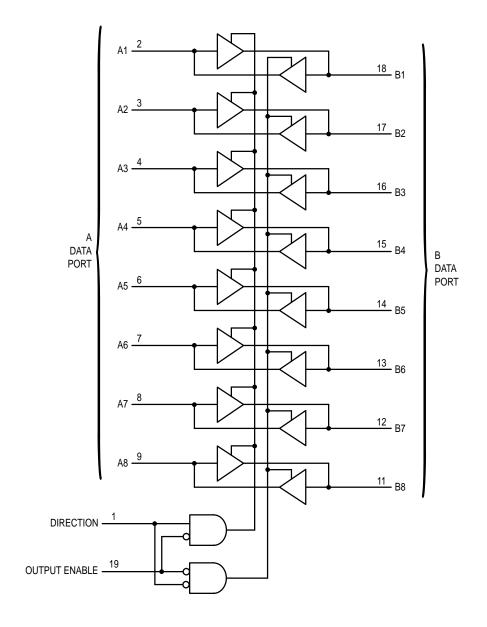
 $\begin{array}{c|c} & \text{TEST POINT} \\ \hline \\ \text{DEVICE} \\ \text{UNDER} \\ \text{TEST} \end{array} \begin{array}{c} \text{OUTPUT} & \text{$1\,\text{k}\Omega$} \\ \hline \\ \text{C_L^*} \end{array} \begin{array}{c} \text{CONNECT TO V_CC WHEN } \\ \text{TESTING tp}_\text{LZ} \text{ AND tp}_\text{ZL}. \\ \text{CONNECT TO GND WHEN } \\ \text{TESTING tp}_\text{LZ} \text{ AND tp}_\text{ZH}. \end{array}$

Figure 3. Figure 4.

3 MOTOROLA

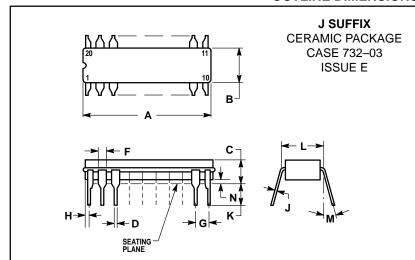
^{*} Includes all probe and jig capacitance

EXPANDED LOGIC DIAGRAM



MOTOROLA

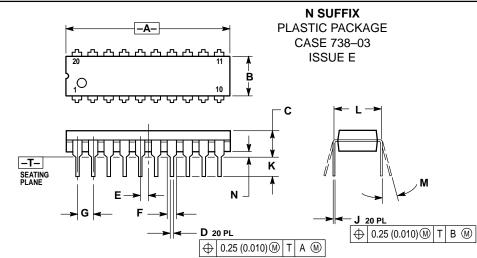
OUTLINE DIMENSIONS



- NOTES:

 1. LEADS WITHIN 0.25 (0.010) DIAMETER, TRUE
 POSITION AT SEATING PLANE, AT MAXIMUM
 MATERIAL CONDITION.
- 2. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
 3. DIMENSIONS A AND B INCLUDE MENISCUS.

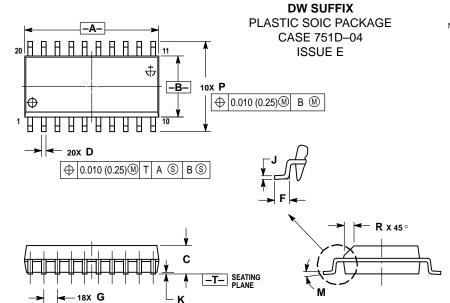
| | MILLIMETERS | | INC | HES | |
|-----|-------------|----------|-------|-------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 23.88 | 25.15 | 0.940 | 0.990 | |
| В | 6.60 | 7.49 | 0.260 | 0.295 | |
| O | 3.81 | 5.08 | 0.150 | 0.200 | |
| D | 0.38 | 0.56 | 0.015 | 0.022 | |
| F | 1.40 | 1.65 | 0.055 | 0.065 | |
| G | 2.54 BSC | | 0.100 | BSC | |
| Н | 0.51 | 1.27 | 0.020 | 0.050 | |
| ۲ | 0.20 | 0.30 | 0.008 | 0.012 | |
| K | 3.18 | 4.06 | 0.125 | 0.160 | |
| Г | 7.62 | 7.62 BSC | | BSC | |
| M | 0 ° | 15° | 0° | 15° | |
| N | 0.25 | 1.02 | 0.010 | 0.040 | |



NOTES:

- IOLES:
 1 DIMENSIONING AND TOLERANCING PER ANSI
 Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEAD WHEN
 FORMED PARALLEL.
 4. DIMENSION B DOES NOT INCLUDE MOLD
- FLASH.

| | INCHES | | MILLIN | IETERS |
|-----|-----------|-------|----------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 1.010 | 1.070 | 25.66 | 27.17 |
| В | 0.240 | 0.260 | 6.10 | 6.60 |
| С | 0.150 | 0.180 | 3.81 | 4.57 |
| D | 0.015 | 0.022 | 0.39 | 0.55 |
| Е | 0.050 | BSC | 1.27 | BSC |
| F | 0.050 | 0.070 | 1.27 | 1.77 |
| G | 0.100 BSC | | 2.54 | BSC |
| J | 0.008 | 0.015 | 0.21 | 0.38 |
| K | 0.110 | 0.140 | 2.80 | 3.55 |
| L | 0.300 | BSC | 7.62 BSC | |
| M | 0° | 15° | 0° | 15° |
| N | 0.020 | 0.040 | 0.51 | 1.01 |



5

- OTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

 4. MAXIMUM MOLD PROTRUSION 0.150

- 4. MAXIMUM MOLD PROTRUSION 0.130
 (0.006) PER SIDE.

 5. DIMENSION D DOES NOT INCLUDE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.13 (0.005) TOTAL IN EXCESS OF D DIMENSION AT MAXIMUM MATERIAL CONDITION.

| | MILLIMETERS | | INC | HES |
|-----|-------------|-------|-------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 12.65 | 12.95 | 0.499 | 0.510 |
| В | 7.40 | 7.60 | 0.292 | 0.299 |
| С | 2.35 | 2.65 | 0.093 | 0.104 |
| D | 0.35 | 0.49 | 0.014 | 0.019 |
| F | 0.50 | 0.90 | 0.020 | 0.035 |
| G | 1.27 | BSC | 0.050 | BSC |
| J | 0.25 | 0.32 | 0.010 | 0.012 |
| K | 0.10 | 0.25 | 0.004 | 0.009 |
| M | 0 ° | 7 ° | 0 ° | 7° |
| Р | 10.05 | 10.55 | 0.395 | 0.415 |
| R | 0.25 | 0.75 | 0.010 | 0.029 |

MC54/74HC245A

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